



## DOCUMENT CHANGE REQUEST

DCR number            75            Changes required for: Qualification  
Date: 2008/01/11            Date sent: 2008/01/11  
Status: IMPLEMENTED

Originator: Marielle BELASIC  
Organisation: CNES

Title: Transistors High Voltage NPN, based on type 2N5551

Number: 5201/019            Issue: 1

Other documents affected:

Page:

See attached file.

Paragraph:

See attached file.

Original wording:


Proposed wording:

See attached file

Justification:

During transfer from 4"(STMicroelectronics Catania) to 5" (ST Singapore) wafers, some diffusion lines have not been reconducted due to the low market needs. But in order to avoid any devices obsolescence for space market. ST Rennes has conducted a qualification on the S111 line in 5" wafer which replace 5551 line 4" wafer. All the tests parameters are in full compliance with the detail specification except two AC parameters (forward current transfer ratio 2; emitter-base capacitance).

A PCN has been raised by STMicroelectronics to advise their customers and they didn't receive any comments concerning these electrical performances changes.

Attachments:
N/A
Modifications:
N/A
Approval signature:

Date signed:
2008-01-11